P-channel Enhancement Mode Power MOSFET

Features

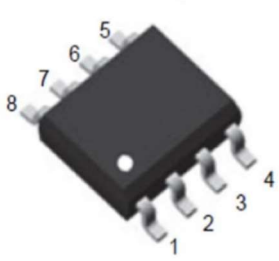
- VDS= -40V, ID= -13A
  RDS(ON) < 12mΩ @ VGS = -10V
  RDS(ON) < 14mΩ @ VGS = -4.5V

General Features

- Advanced Trench Technology
- Provide Excellent RDS(ON) and Low Gate Charge
- Lead Free and Green Available

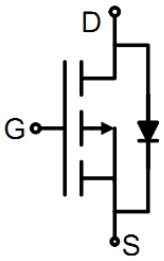
100% UIS TESTED!
100% ΔVds TESTED!

RoHS



SOP-8

pin assignment



Schematic diagram

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-40	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	-13	A
Drain Current-Continuous(T_C=100℃)	I_D (100℃)	-9	A
Pulsed Drain Current	I_{DM}	50	A
Maximum Power Dissipation	P_D	2.5	W
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance ,Junction-to-Ambient(Note 2)	$R_{\theta JA}$	50	℃/W

Electrical Characteristics (T_A=25℃unless otherwise noted)

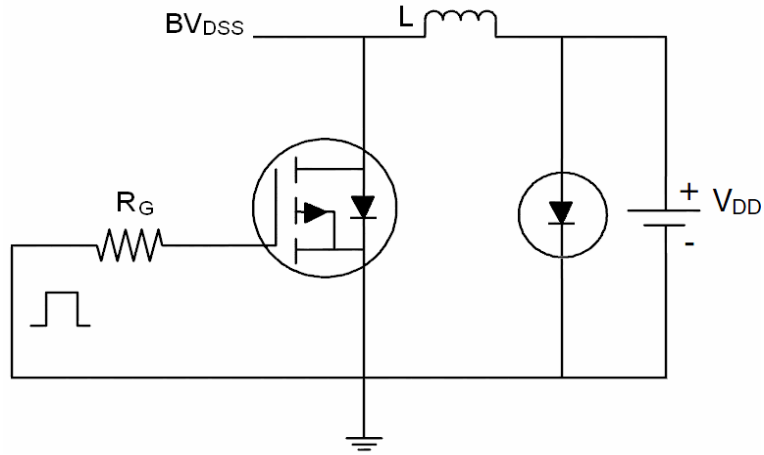
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=-250μA	-40	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-40V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250μA	-1.0		-3.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-12A	-		12	mΩ
Forward Transconductance	g_{FS}	V_{DS}=-15V,I_D=-10A	35	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=-20V,V_{GS}=0V, F=1.0MHz	-	2800	-	PF
Output Capacitance	C_{oss}		-	320	-	PF
Reverse Transfer Capacitance	C_{rss}		-	220	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=-20V, ,R_L=2Ω V_{GS}=-10V,R_{GEN}=6Ω	-	11	-	nS
Turn-on Rise Time	t_r		-	75	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	89	-	nS
Turn-Off Fall Time	t_f		-	35	-	nS
Total Gate Charge	Q_g	V_{DS}=-20V,I_D=-12A, V_{GS}=-10V	-	40	-	nC
Gate-Source Charge	Q_{gs}		-	6	-	nC
Gate-Drain Charge	Q_{gd}		-	12	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=-12A	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	-13	A

Notes:

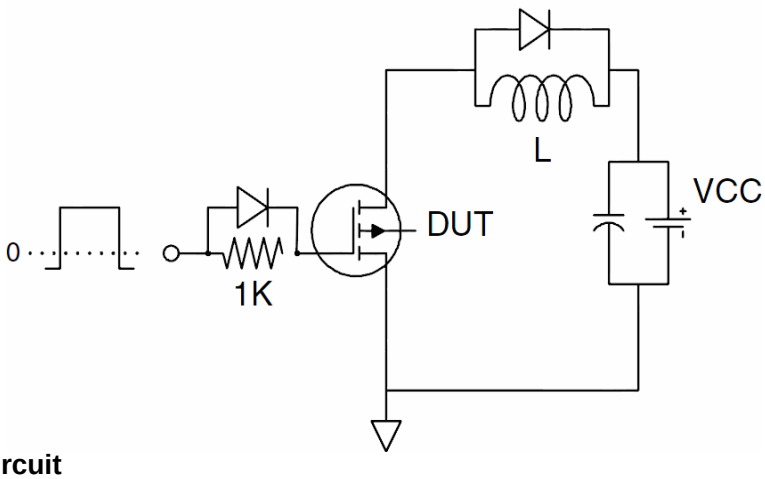
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Test Circuit

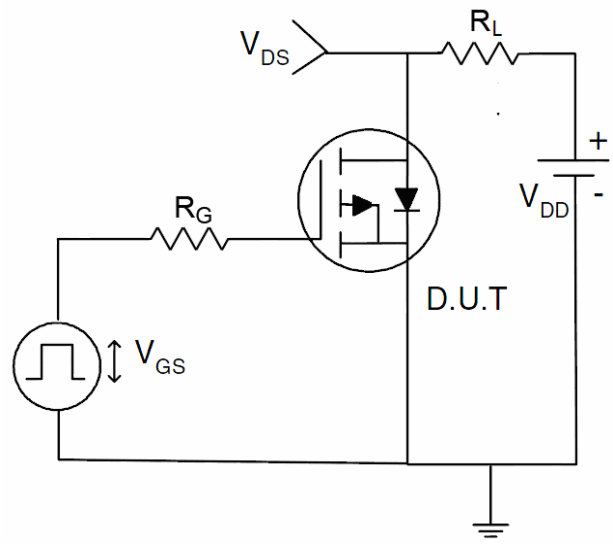
1) E_{AS} Test Circuit



2) Gate Charge Test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

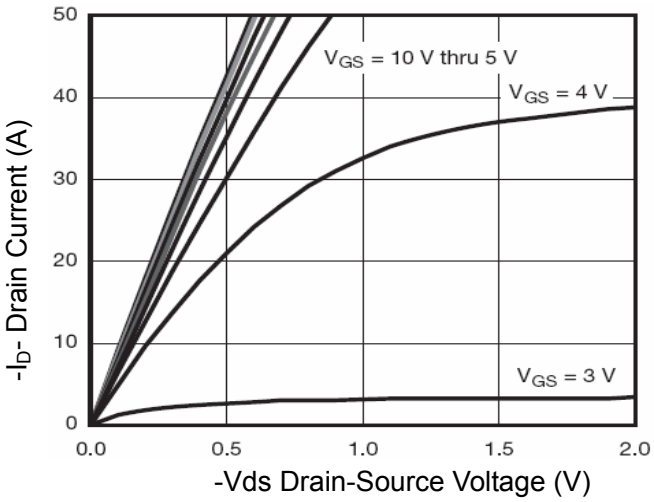


Figure 1 Output Characteristics

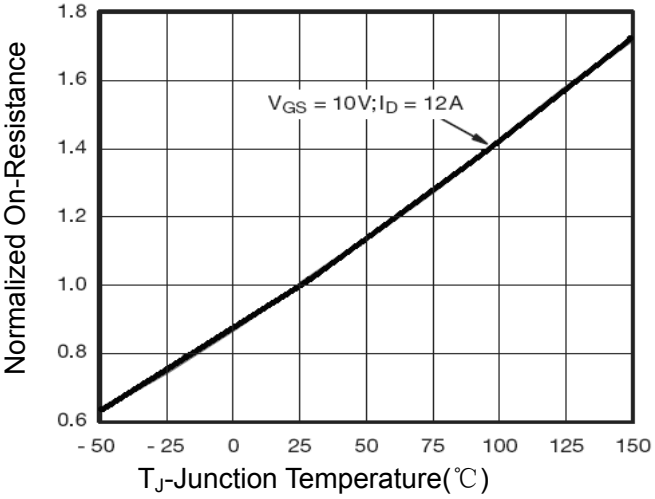


Figure 4 Rdson-Junction Temperature

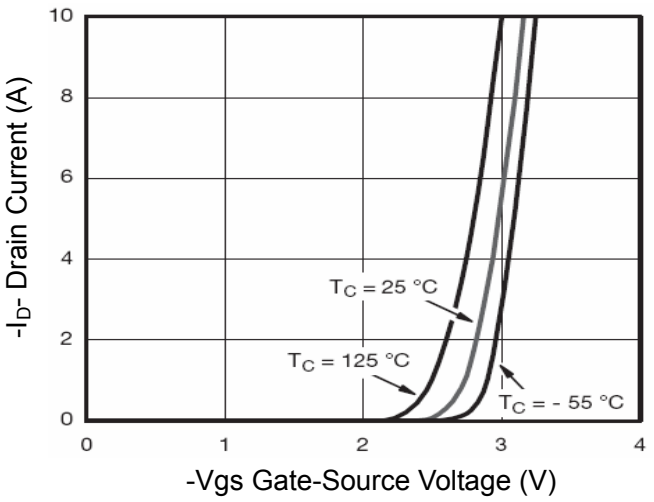


Figure 2 Transfer Characteristics

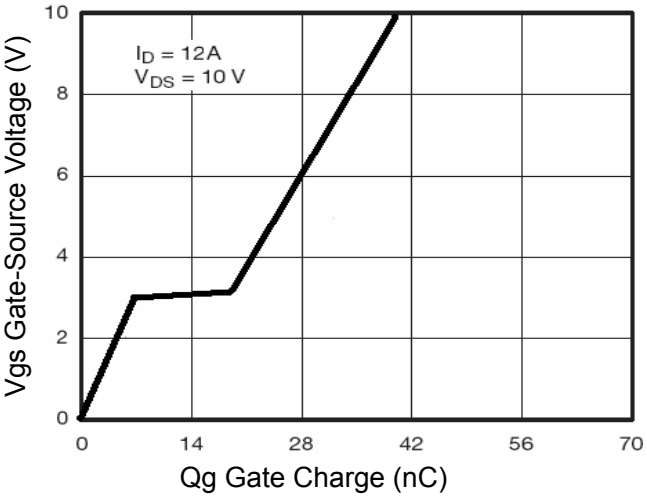


Figure 5 Gate Charge

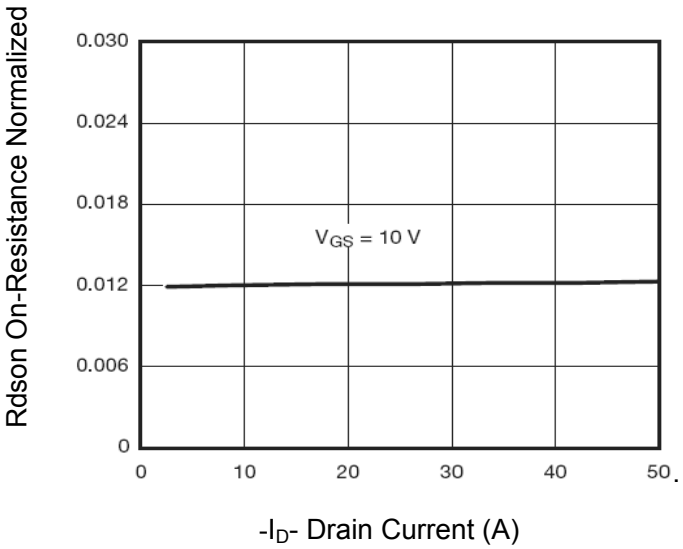


Figure 3 Rdson- Drain Current

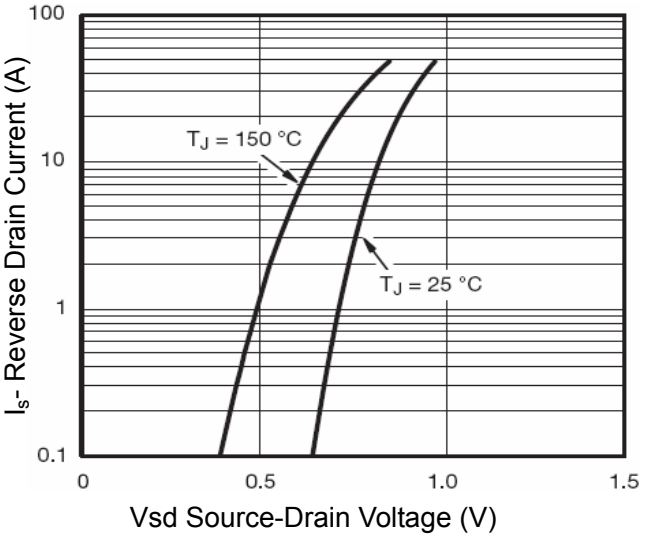


Figure 6 Source- Drain Diode Forward

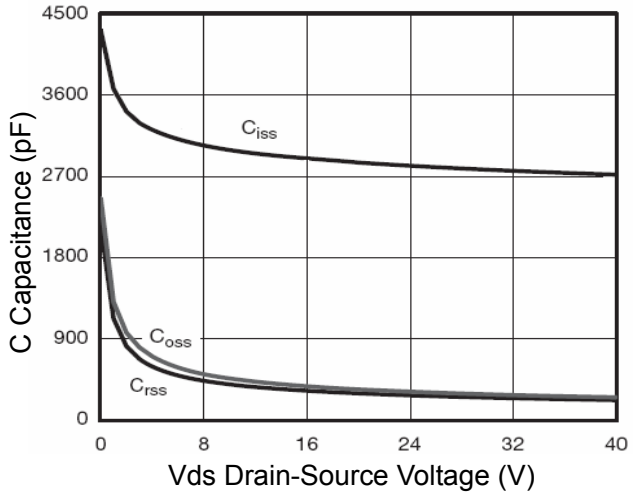


Figure 7 Capacitance vs Vds

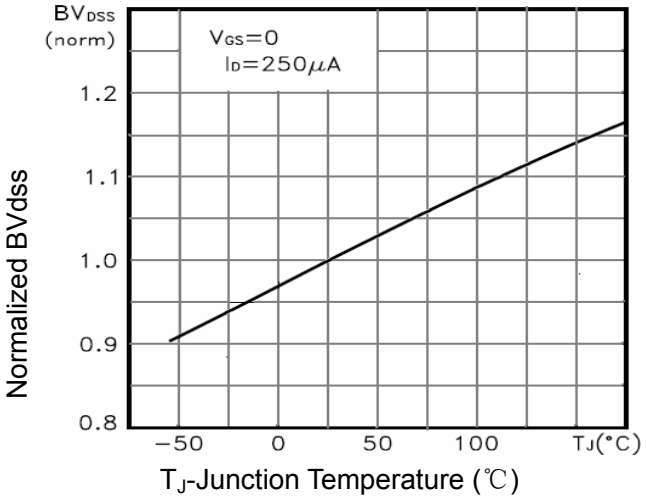


Figure 9 BV_{DSS} vs Junction Temperature

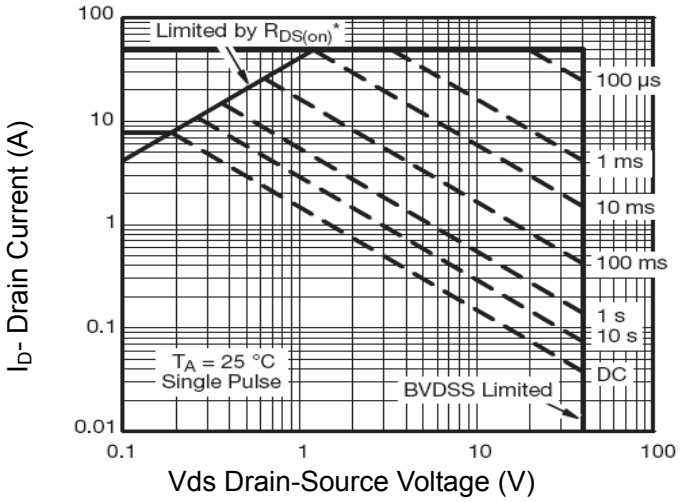


Figure 8 Safe Operation Area

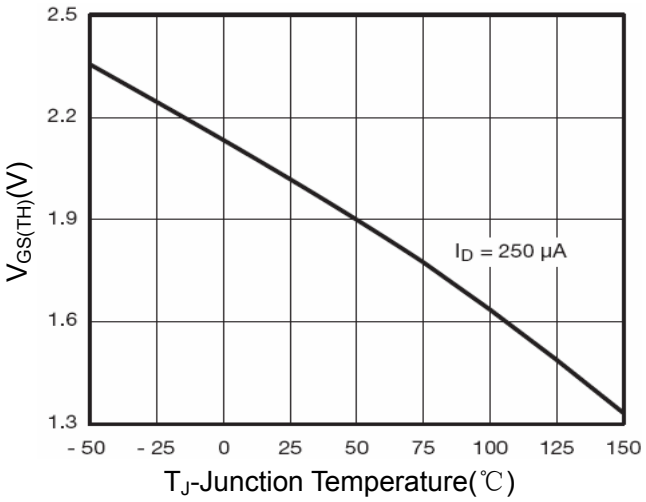


Figure 10 $V_{GS(th)}$ vs Junction Temperature

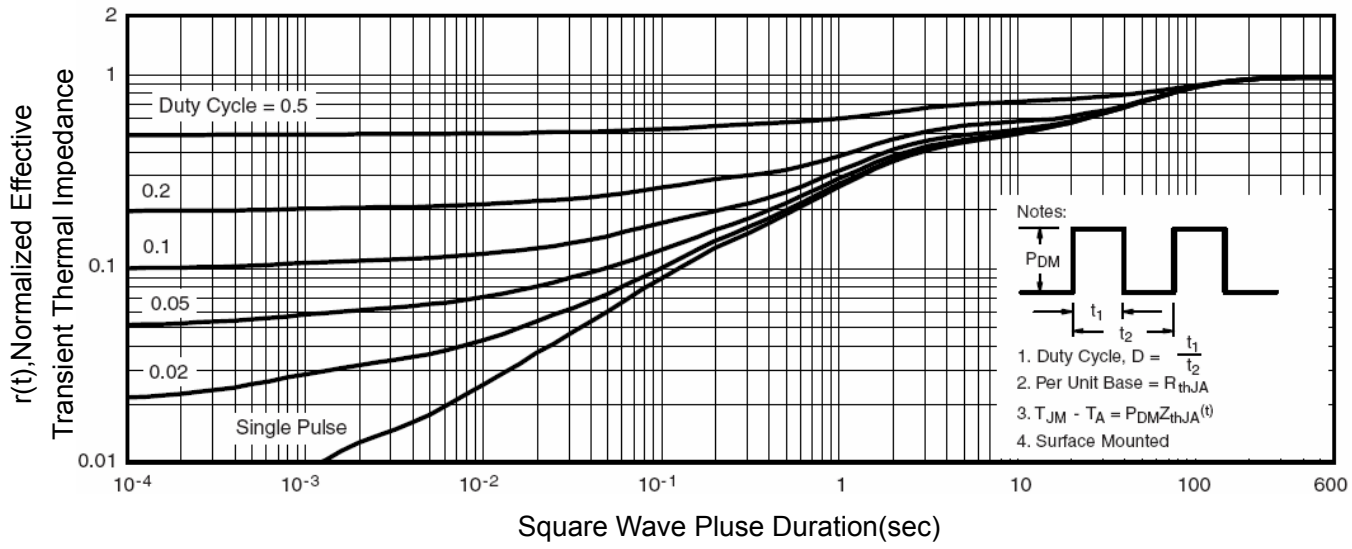


Figure 11 Normalized Maximum Transient Thermal Impedance